

TOSHIBA FIELD EFFECT TRANSISTOR SILICON N CHANNEL DUAL GATE MOS TYPE

# 3SK199

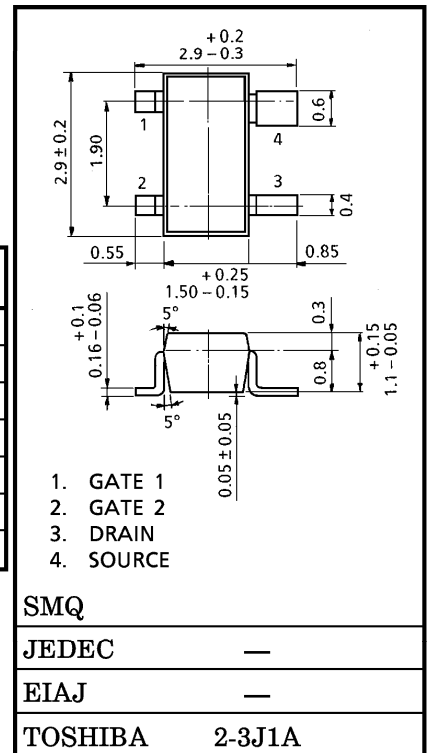
TV TUNER, UHF RF AMPLIFIER APPLICATIONS

Unit in mm

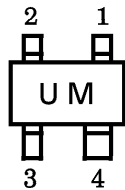
- Superior Cross Modulation Performance.
- Low Reverse Transfer Capacitance :  $C_{RSS} = 0.015\text{pF}$  (Typ.)
- Low Noise Figure :  $NF = 1.9\text{dB}$  (Typ.)

MAXIMUM RATINGS ( $T_a = 25^\circ\text{C}$ )

| CHARACTERISTIC            | SYMBOL    | RATING         | UNIT             |
|---------------------------|-----------|----------------|------------------|
| Drain-Source Voltage      | $V_{DS}$  | 13.5           | V                |
| Gate 1-Source Voltage     | $V_{G1S}$ | $\pm 8$        | V                |
| Gate 2-Source Voltage     | $V_{G2S}$ | $\pm 8$        | V                |
| Drain Current             | $I_D$     | 30             | mA               |
| Drain Power Dissipation   | $P_D$     | 150            | mW               |
| Channel Temperature       | $T_{ch}$  | 125            | $^\circ\text{C}$ |
| Storage Temperature Range | $T_{stg}$ | $-55 \sim 125$ | $^\circ\text{C}$ |



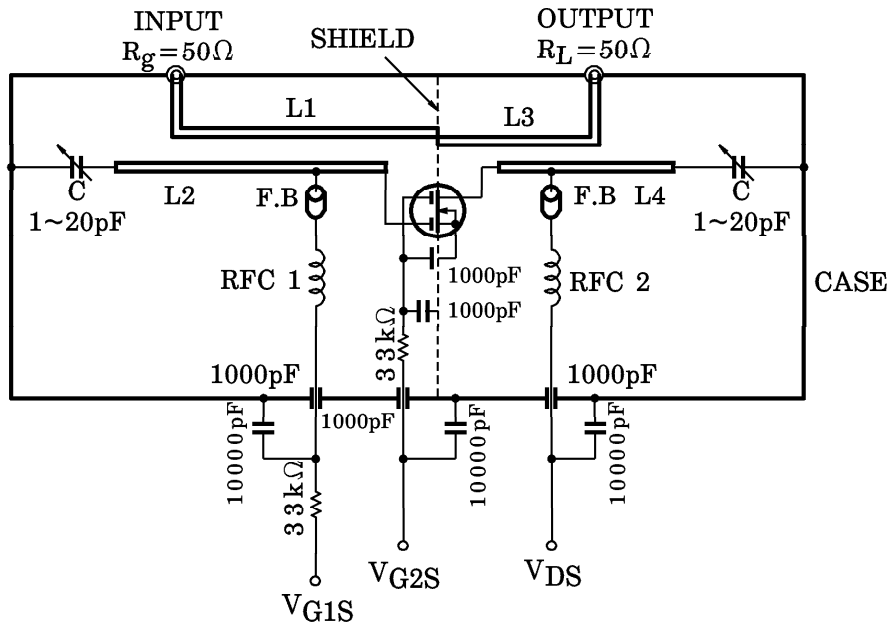
Marking



Weight : 0.013g

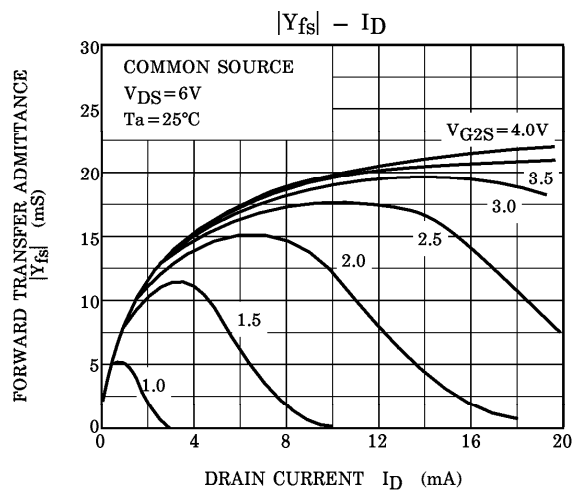
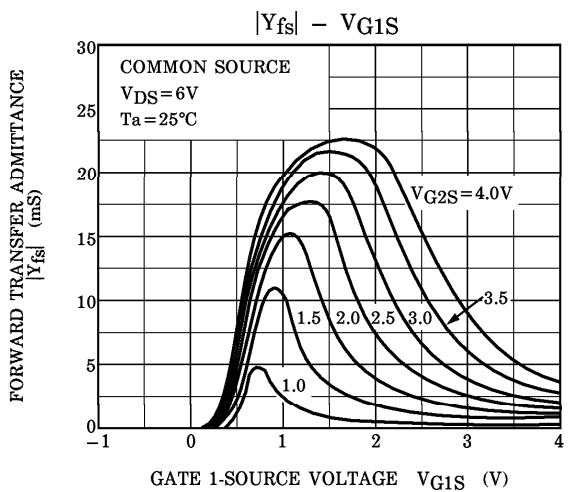
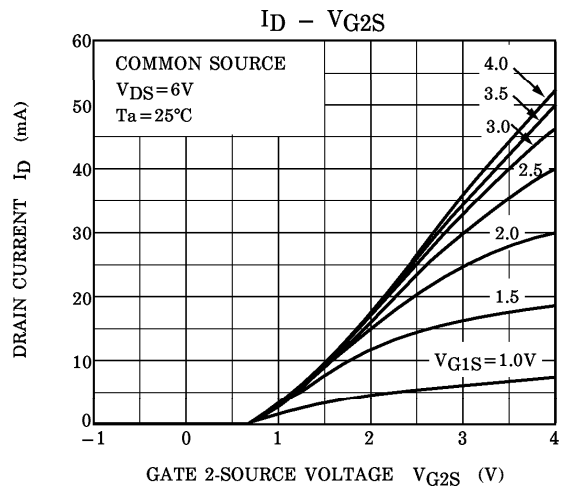
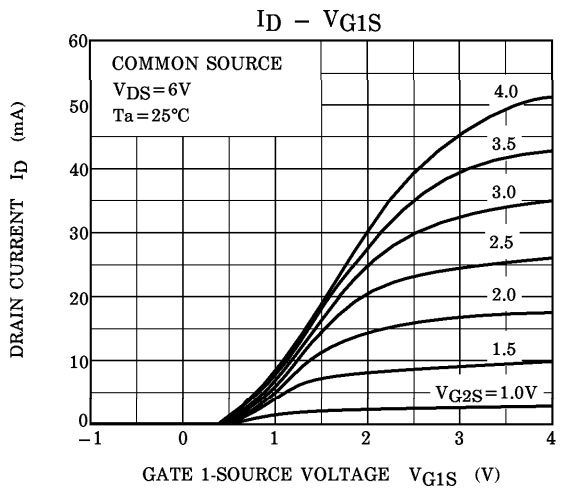
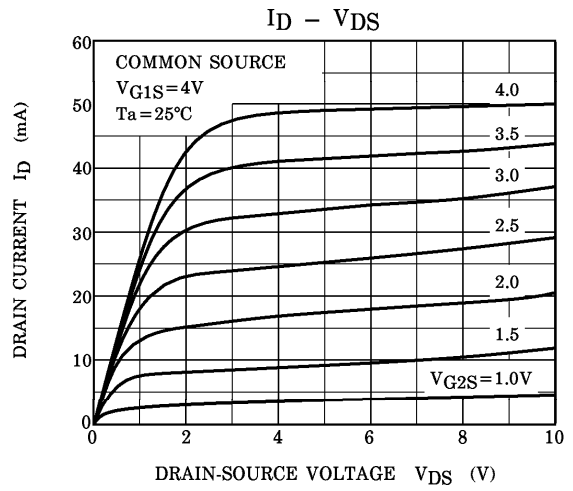
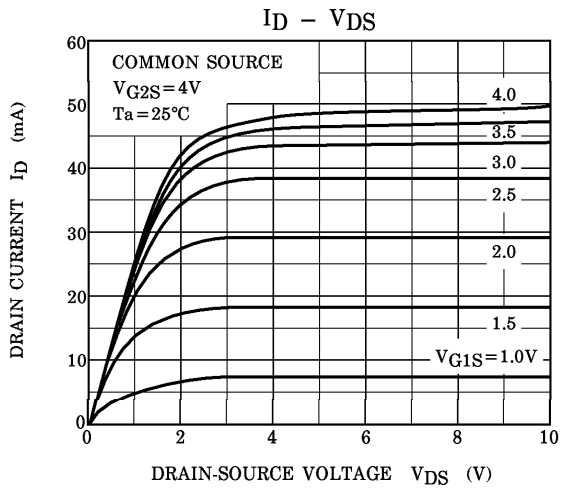
ELECTRICAL CHARACTERISTICS ( $T_a = 25^\circ\text{C}$ )

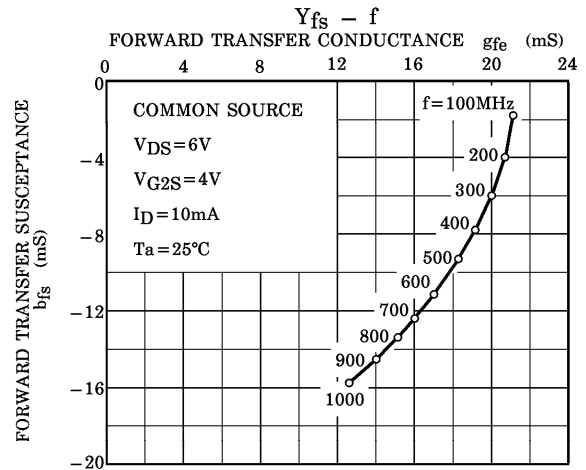
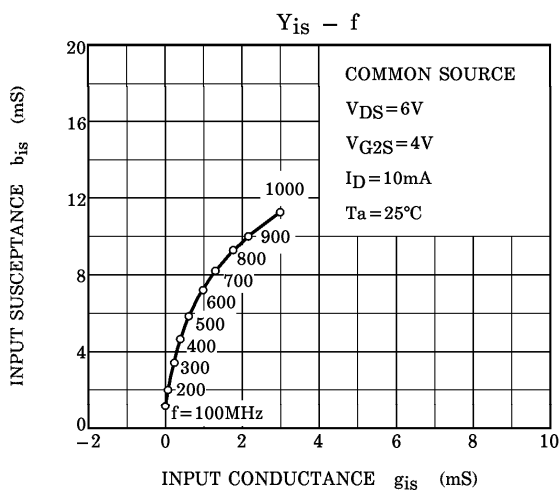
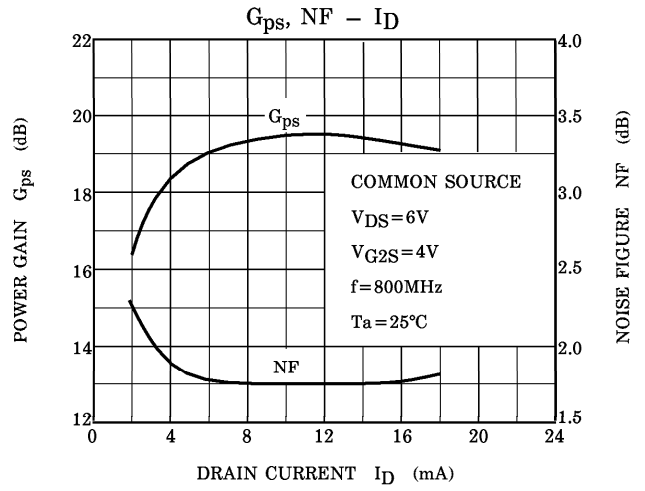
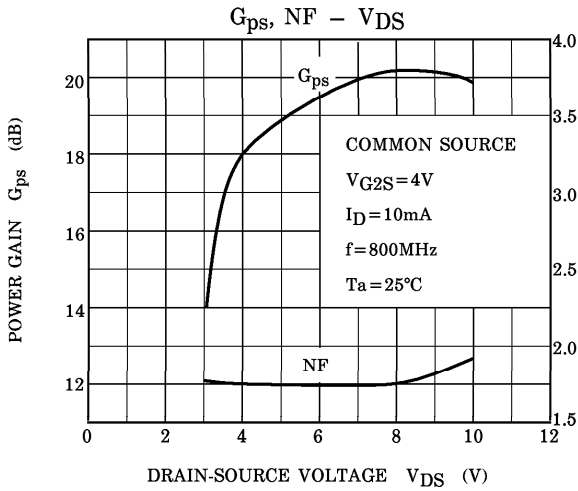
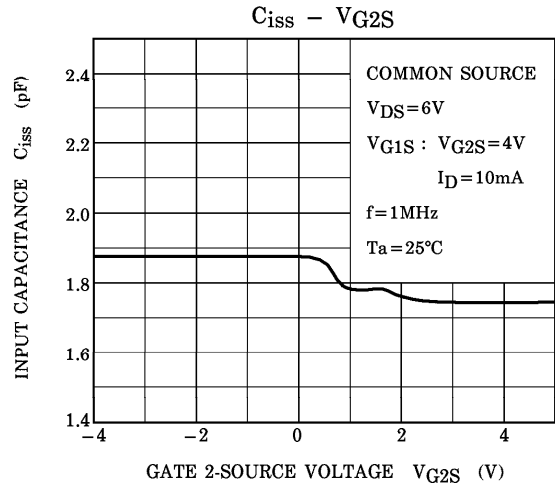
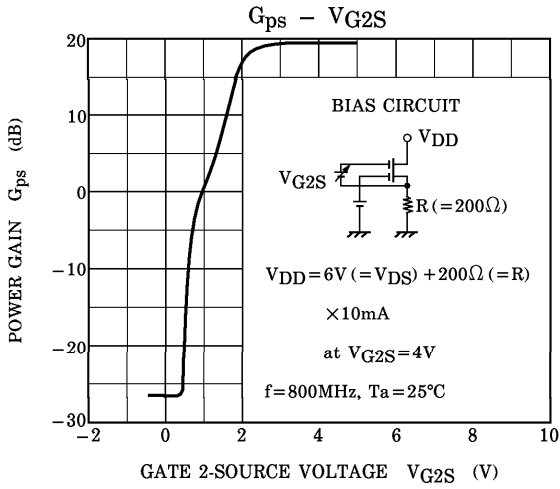
| CHARACTERISTIC                | SYMBOL         | TEST CONDITION  | MIN. | TYP.  | MAX.     | UNIT |
|-------------------------------|----------------|---|------|-------|----------|------|
| Gate 1 Leakage Current        | $I_{G1SS}$     | $V_{DS} = 0, V_{G1S} = \pm 6\text{V}, V_{G2S} = 0$                                      | —    | —     | $\pm 50$ | nA   |
| Gate 2 Leakage Current        | $I_{G2SS}$     | $V_{DS} = 0, V_{G1S} = 0, V_{G2S} = \pm 6\text{V}$                                      | —    | —     | $\pm 50$ | nA   |
| Drain-Source Voltage          | $V_{(BR)DSX}$  | $V_{G1S} = -4\text{V}, V_{G2S} = -4\text{V}, I_D = 100\mu\text{A}$                      | 13.5 | —     | —        | V    |
| Drain Current                 | $I_{DSS}$      | $V_{DS} = 6\text{V}, V_{G1S} = 0, V_{G2S} = 4\text{V}$                                  | 0    | —     | 0.1      | mA   |
| Gate 1-Source Cut-off Voltage | $V_{G1S(OFF)}$ | $V_{DS} = 6\text{V}, V_{G2S} = 4\text{V}, I_D = 100\mu\text{A}$                         | 0    | —     | 1.0      | V    |
| Gate 2-Source Cut-off Voltage | $V_{G2S(OFF)}$ | $V_{DS} = 6\text{V}, V_{G1S} = 4\text{V}, I_D = 100\mu\text{A}$                         | 0    | —     | 1.2      | V    |
| Forward Transfer Admittance   | $ Y_{fs} $     | $V_{DS} = 6\text{V}, V_{G2S} = 4\text{V}, I_D = 10\text{mA}, f = 1\text{kHz}$           | —    | 21.5  | —        | mS   |
| Input Capacitance             | $C_{iss}$      | $V_{DS} = 6\text{V}, V_{G2S} = 4\text{V}, I_D = 10\text{mA}, f = 1\text{MHz}$           | 1.0  | 1.6   | 2.4      | pF   |
| Reverse Transfer Capacitance  | $C_{rss}$      | $I_D = 10\text{mA}, f = 1\text{MHz}$  | —    | 0.015 | 0.03     | pF   |
| Power Gain                    | $G_{ps}$       | $V_{DS} = 6\text{V}, V_{G2S} = 4\text{V}, I_D = 10\text{mA}, f = 800\text{MHz}$ (Fig.1) | 18   | 19.5  | —        | dB   |
| Noise Figure                  | NF             |   | —    | 1.9   | 3.0      | dB   |

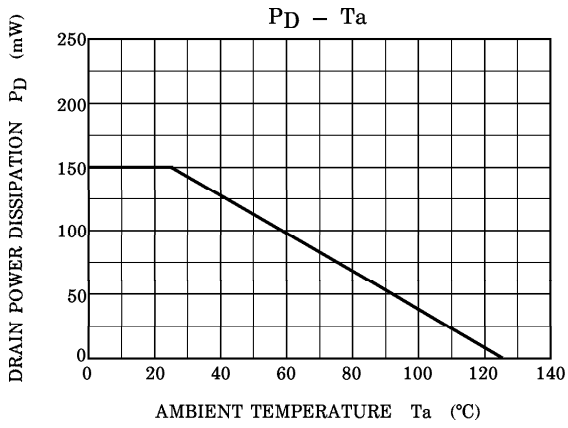
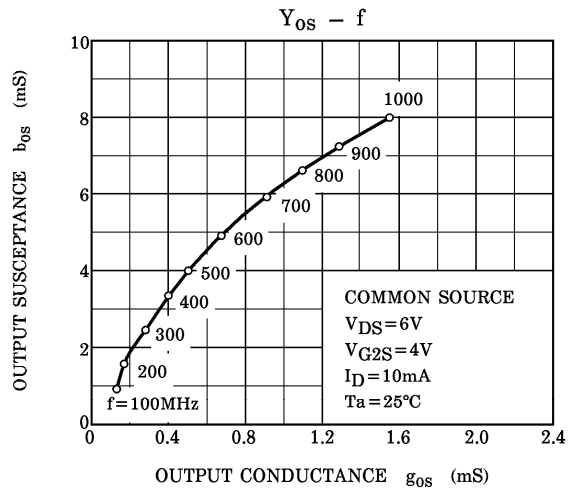
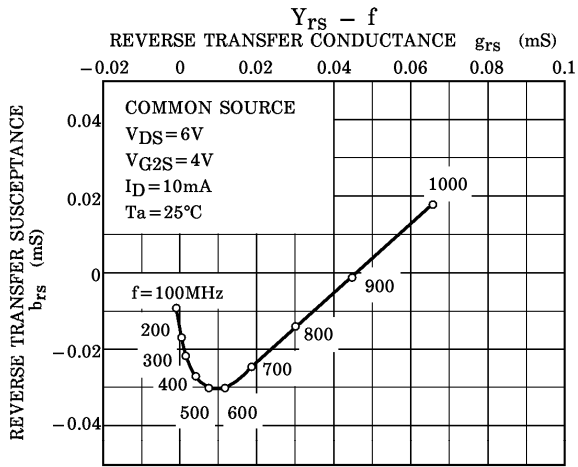


- L1~L4 :  $\phi$ 0.8mm SILVER PLATED COPPER WIRE
- C : AIR TRIMMER TTA25A200A (MURATA MFG. Co., Ltd.)
- RFC 1 :  $\phi$ 0.35mm COPPER WIRE 3mm ID, 7T
- RFC 2 :  $\phi$ 0.35mm COPPER WIRE 3mm ID, 10T

Fig.1 800MHz  $G_{ps}$ , NF TEST CIRCUIT







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